Ordering number:EN1065C

GMA01, 01U

Epitaxial Planar Silicon Diode

Very High-Speed Switching, Bias Stabilizing Applications

Features

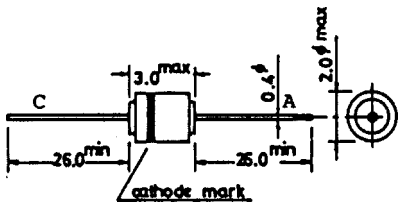
- Glass sleeve structure.
- Allowable power dissipation : P=300mW max.
- Interterminal capacitance : c=3.0pF max.
- Reverse recovery time : t_{rr}=4.0ns max.
- Small size, being about half of DO-35 package heretofore in use.

Package Dimensions

unit:mm

1114

[GMA01, 0U]



C:Cathode
A:Anode

Specifications

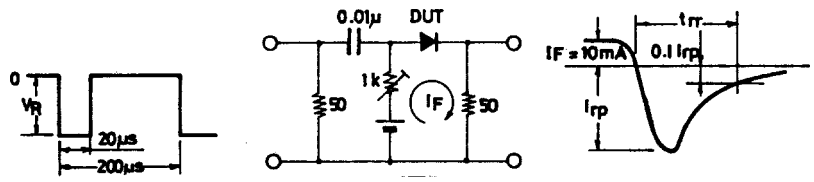
Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	GMA01	GMA01U	Unit
Peak Reverse Voltage	V_{RM}		60	105	V
Reverse Voltage	V_R		55	100	V
Peak Forward Current	I_{FM}		→	360	mA
Average Rectified Current	I_O		→	120	mA
Surge Forward Current	I_{FSM}	1 s pulse	→	500	mA
Allowable Power Dissipation	P		→	300	mW
Junction Temperature	Tj		→	175	˚C
Storage Temperature	Tstg		→	–65 to +175	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V_F	I_F=1.5mA	0.55		0.68	V
Reverse Current	I_R	V_R=55 (GMA01)			0.5	μA
		V_R=75 (GMA01U)			0.5	μA
		V_R=100V (GMA01U)			5	μA
Interterminal Capacitance	C	V_R=0, f=1MHz			3.0	pF
Reverse Recovery TIme	t_{rr}	V_R=6V, I_F=10mA, R_L=50Ω			4.0	ns

Reverse Recovery Time Test Circuit



Unit (resistance : Ω, capacitance : F)